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Attorney's Docket No. 042390.P5771D  
2/23/01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Gang Bai and Chunlin Liang

Serial No. 09/517,705

Filed: March 2, 2000

For: *Complementary Metal Gate Electrode Technology*

Divisional Application of:

Serial No. 09/107,604

Filed: June 30, 1998

Examiner: Not yet assigned

Art Unit 2811

RECEIVED  
JAN 25 2001  
TC 2800 MAIL ROOM

RECEIVED  
JAN 17 2001  
TC 2800 MAIL ROOM

RECEIVED  
JAN 30 2001  
TC 3700 MAIL ROOM

SUPPLEMENTAL PRELIMINARY AMENDMENT

Box Amendments - No Fee

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

In connection with the above-referenced Divisional Application under Rule 1.53(b),

Applicants respectfully request entry of the following amendments.

IN THE SPECIFICATION

At page 1, line 3, please replace "The", first occurrence, with -In the context of insulated

B1 gate field effect transistors, the--.

At page 1, line 11, please replace "can significantly eliminate" with --may reduce--.

At page 1, line 15, please replace "can" with --may--.

At page 1, line 18, after "etc.", please insert -Longer gate electrodes correspond to field

B2 effect transistors of greater width.--.